

## Standard Rectifier Module

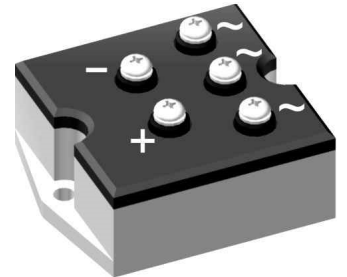
# PHASE OUT

3~ Rectifier Bridge

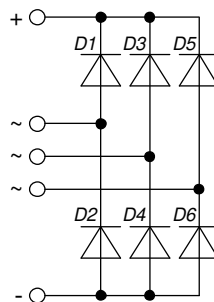
<b>3~ Rectifier</b>	
$V_{RRM}$	= 1600 V
$I_{DAV}$	= 60 A
$I_{FSM}$	= 750 A

Part number

**VUO55-16NO7**



 E72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: PWS-B

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Aluminium internally DCB isolated
- Advanced power cycling

**Recommended replacement: VUO82-16NO7, VUO84-16NO7**

### Disclaimer Notice

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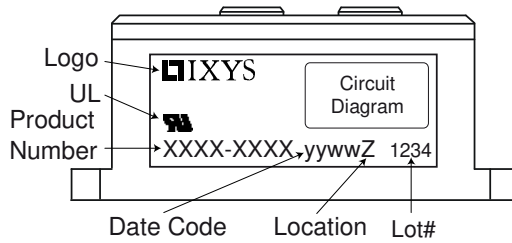


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
$V_F$	forward voltage drop	$I_F = 20$ A		$T_{VJ} = 25^\circ\text{C}$		1.03	V
		$I_F = 60$ A				1.23	V
		$I_F = 20$ A		$T_{VJ} = 125^\circ\text{C}$		0.92	V
		$I_F = 60$ A				1.18	V
$I_{DAV}$	bridge output current	$T_C = 85^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		60	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.76	V
$r_F$	slope resistance	} for power loss calculation only				6.9	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					2.7	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.4		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		46	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		750	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		810	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		640	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		690	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		2.82	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		2.73	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		2.05	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.98	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF

# PHASE OUT



Package PWS-B				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			100	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		125	°C	
<b>Weight</b>				203		g	
$M_D$	mounting torque		4.25		5.75	Nm	
$M_T$	terminal torque		2.5		3.5	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	11.0			mm	
$d_{Spb/Apb}$		terminal to backside	7.5			mm	
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V	
		t = 1 minute	2500			V	



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO55-16NO7	VUO55-16NO7	Box	10	456691

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$

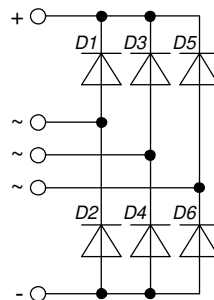
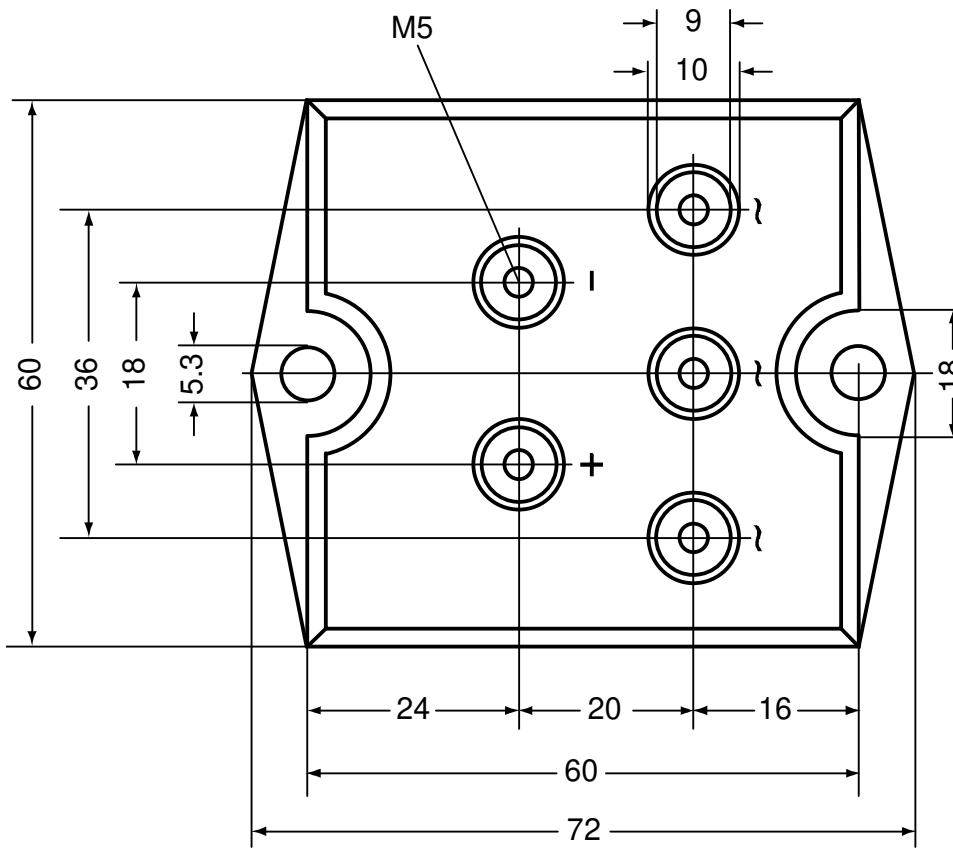
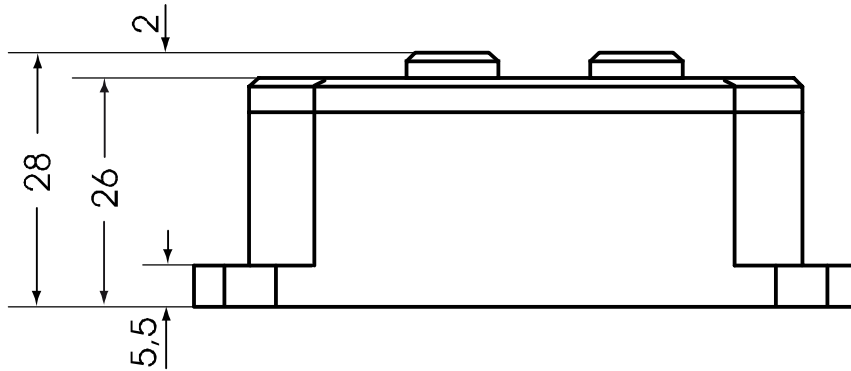


**Rectifier**

$V_{0\ max}$	threshold voltage	0.76	V
$R_{0\ max}$	slope resistance *	5.7	mΩ



**Outlines PWS-B**





**Rectifier**

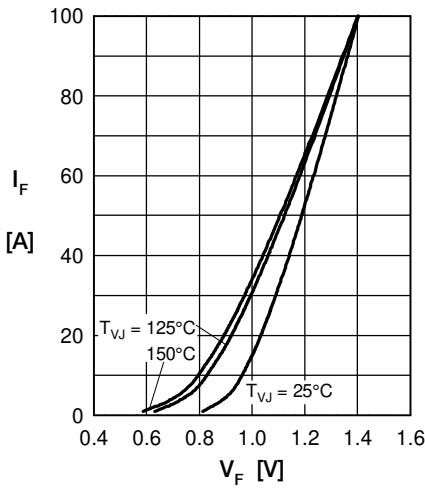


Fig. 1 Forward current vs. voltage drop per diode

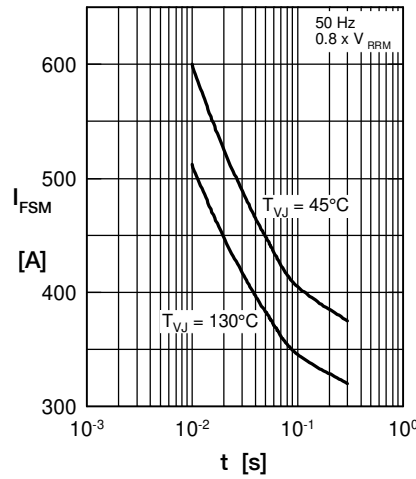


Fig. 2 Surge overload current vs. time per diode

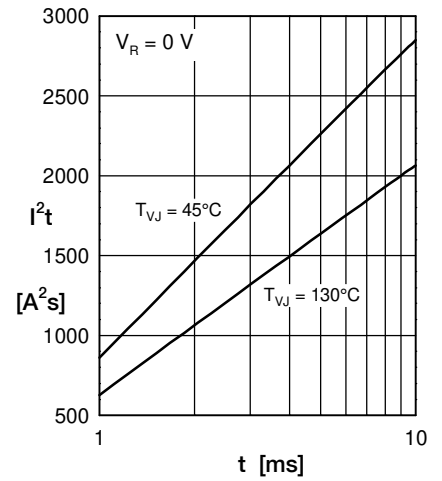


Fig. 3  $I^2t$  vs. time per diode

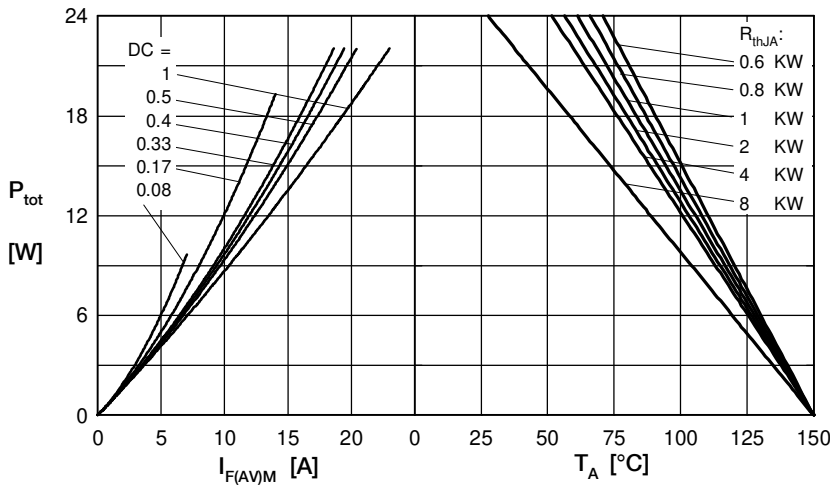


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

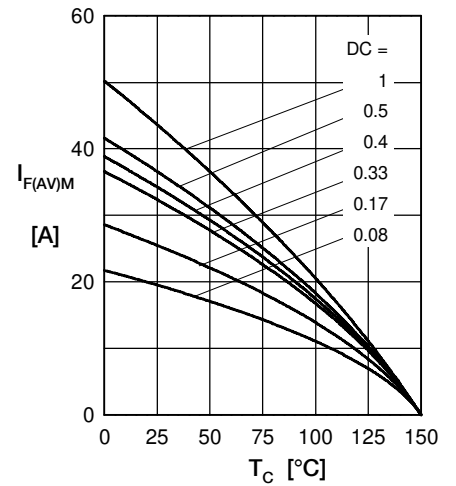


Fig. 5 Max. forward current vs. case temperature per diode

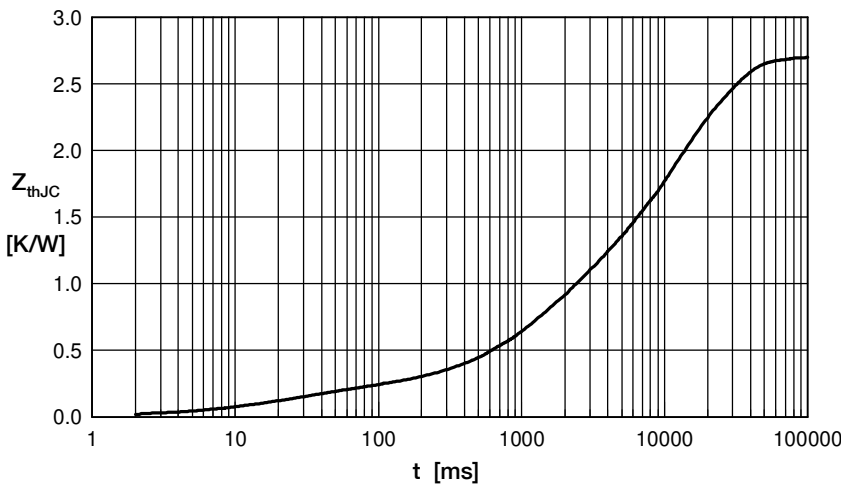


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.040	0.010
2	0.150	0.030
3	0.610	1.350
4	1.900	14.00